

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	261	ishicashi-tadao.in. ando-seigo.in. tsuzuki-ken.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 13:50
L2	261	ishicashi-tadao.in. ando-seigo.in. tsuzuki-ken.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 13:50
L3	261	ishicashi-tadao.in. ando-seigo.in. tsuzuki-ken.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/18 13:50
S7	0	"5799027".pn. and impurit	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/30 15:44
S8	0	"5799027".pn. and deplet	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/30 15:45
S9	2	"5799027".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/07/30 15:45
S13	2293	385/131-132.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/15 12:50
S14	2	"10574513"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/15 13:28

S15	8037	372/43.01-50.23.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/15 15:14
S16	8483	257/183-201.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/15 15:18
S17	812	semiconductor near4 waveguide same (n p) near4 type	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/15 15:24
S18	260	ishicashi-tadao.in. ando-seigo. in. tsuzuki-ken.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/16 07:22
S19	36	("257".clas. "385".clas. "372". clas.) and semiconductor near4 waveguide and pn near3 junction and (n near2 i near2 n "n-i-n" nin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/16 09:41
S20	43	semiconductor near4 waveguide and pn near3 junction and (n near2 i near2 n "n-i-n" nin)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/16 10:39
S21	7	S20 not S19	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/16 10:39
S22	18	semiconductor near4 waveguide same "n" near2 electrode and pn near3 junction	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/16 11:19
S23	15	S22 not S19	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/16 11:19

S24	0	("2007/0172184").URPN.	USPAT	OR	ON	2009/01/16 12:13
S25	9619	385/2,8,40,129-132.ccls. 359/245,247,248,276.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/16 13:32
S26	294	S25 and "n" near2 electrode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/16 13:35
S27	16	S25 and ("nin" "N-I-N" "n-i-n")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/16 13:36
S28	189	S25 and pn near2 junction	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/16 13:36
S29	3	S26 and S27	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/16 13:36
S30	2	S27 and S28	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/16 14:02
S31	40	S26 and S28	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/16 14:03
S32	38	S31 not S27	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/16 14:40

S33	2	"10574513"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/16 14:42
S34	2	"20020122615"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/12 15:01
S35	261	ishicashi-tadao.in. ando-seigo. in. tsuzuki-ken.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/13 08:09
S36	261	ishicashi-tadao.in. ando-seigo. in. tsuzuki-ken.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/13 08:09
S37	0	S35 not S36	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/13 08:09
S38	2	(n near2 type near5 electrode and p near2 type and semiconductor and (bandgap band near2 gap) near3 (greater less more) and semiconductor near2 core). clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/13 08:21
S39	2	(n near2 type near5 electrode and p near2 type and semiconductor and (bandgap band near2 gap) near3 (greater less more) with (waveguide core)).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/13 08:24
S40	35	(n near2 type near5 electrode and p near2 type and semiconductor and (bandgap band near2 gap) near3 (greater less more)).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/13 08:24

S41	23	(n near2 type near3 electrode and p near2 type and semiconductor and (bandgap band near2 gap) near3 (greater less more)).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/13 08:36
S42	18	(n near2 type near2 electrode and p near2 type and semiconductor and (bandgap band near2 gap) near3 (greater less more)).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/05/13 08:37

5/ 18/ 2009 2:34:24 PM

C:\ Documents and Settings\ csmith2\ My Documents\ EAST\ Workspaces\ 10574513
(semiconductor optoelectronic waveguide).wsp